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(54) **FINFET STRUCTURES AND METHODS OF FORMING THE SAME**

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See application file for complete search history.

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(57) **ABSTRACT**

An embodiment is a method including forming an epitaxial portion over a substrate, the epitaxial portion including a III-V material. A damaged material layer being on at least one surface of the epitaxial portion. The method further including oxidizing at least outer surfaces of the damaged material layer to form an oxide layer, selectively removing the oxide layer, and repeating the oxidizing and the selectively removing steps while at least a portion of the damaged material layer remains on the epitaxial portion.

20 Claims, 33 Drawing Sheets

